DIGITAL SYSTEM DESIGN

Dec. 2019/Jan. 2020

Module 1

1. a. Write the truth table of the logic circuit having and imputs a, b and c and an output y = abe + abc + abc. Also simplify the Boolean expression and implement the logic circuit rising NAND gales only. (06 Marks)

Aus! Güren, y = abē + ābc + abc -> Sum of Brodust = \(\sum \left(\text{110}, \text{011}, \text{111} \right) \\ = \(\sum \left(\frac{1}{4} \right) \)
= \(\sum \l

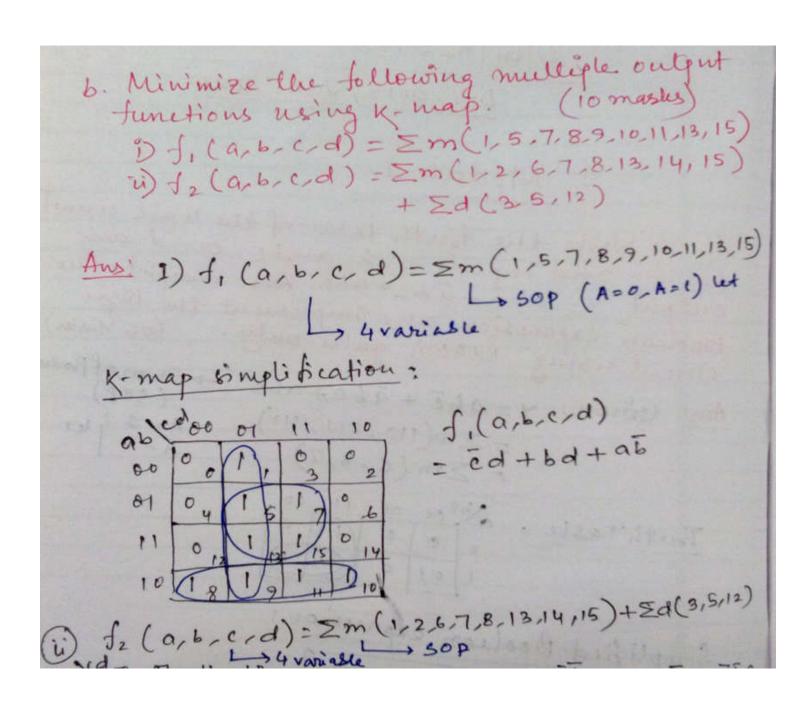
Touth Table: a 6000 of 1100

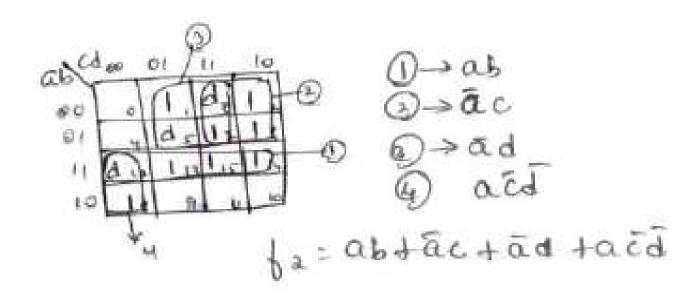
Simplified Boolean expression:

1 y = 6c + ab]

logic circuit using NAND gate only:

7 = 6 c + as 3 - Date - ab. 6 c





c. Défine Canonical Minterm form and canonical Monterm form. (04 masses) Each individual term in standard SOP form is called minterm and each individual term in standard POS form is called maxterm. The concept of minterms and maxterms allows us to introduce a very convenient shorthand notations to express logical functions. Table 1.3.1 gives the minterms and maxterms for a three literal/variable logical function where the number of minterms as well as maxterms is $2^3 = 8$. In general, for an n-variable logical function there are 2^n minterms and an equal number of maxterms.

As shown in Table 1.3.1 each minterm is represented by m_i and each maxterm is represented by M_i, where the subscript i is the decimal number

Va	riab	les	Minterms	Maxterms				
A	В	c	mi	M _i				
0	0	0	$\overline{A} \overline{B} \overline{C} = m_0$	$A+B+C=M_0$				
0	0	1	$\overline{A} \overline{B} C = m_1$	$A+B+\overline{C}=M_1$				
0	1	0	$\overline{A} \ B \ \overline{C} = m_2$	$A + \overline{B} + C = M_2$				
0	1	1	$\overline{A} B C = m_3$	$A + \overline{B} + \overline{C} = M_3$				
1	0	0	$A \overline{B} \overline{C} = m_4$	$\overline{A} + B + C = M_4$				
1	0	1	$A \bar{B} C = m_5$	$\overline{A} + B + \overline{C} = M_5$				
1	1	0	$AB\bar{C}=m_6$	$\overline{A} + \overline{B} + C = M_6$				
1	1	1	A B C = m ₇	$\overline{A} + \overline{B} + \overline{C} = M_7$				

Table 1.3.1 Minterms and maxterms for three variables

equivalent of the natural binary number. With these shorthand notations logical function can be represented as follows:

1.
$$f(A, B, C) = \overline{A} \overline{B} \overline{C} + \overline{A} \overline{B} C + \overline{A} BC + \overline{A} BC$$

 $= m_0 + m_1 + m_3 + m_6$
 $= \sum m(0, 1, 3, 6)$

2.
$$f(A, B, C) = (A + B + \overline{C}) (A + \overline{B} + \overline{C}) (\overline{A} + \overline{B} + C)$$

 $= M_1 \cdot M_3 \cdot M_6$
 $= \Pi M (1, 3, 6)$

where \sum denotes sum of product while Π denotes product of sum.

We know that logical expression can be represented in the truth table form. It is possible to write logic expression in standard SOP or POS form corresponding to a given truth table. The logic expression corresponding to a given truth table can be written in a standard sum of products form by writing one product term for each input combination that produces an output of 1.

			-	
A	В	c	Y	
0	0	0	0	
0	0	1	0	THE PARTY NAMED IN
0	1	0	1	← ABC
0	1	1	1	← ABC
1	0	0	0	3350
1	0	1	0	
1	1	0	1	← AB
1	1	1	0	
	Ta	ble 1	32	

Table 1.3

These product terms are ORed together to create the standard sum of products. The product terms are expressed by writing complement of a variable when it appears as an input 0, and the variable itself when it appears as an input 1. Consider, for example, the truth Table 1.3.2.

The product corresponding to input combination 010 is ABC, the product corresponding to input combination 011 is ABC and product corresponding to input combination 110 is ABC. Thus the standard sum of products form is

$$f(A, B, C) = \overline{A}B\overline{C} + \overline{A}BC + AB\overline{C}$$

= $m_2 + m_3 + m_6$

The logic expression corresponding to a truth table can also be written in a standard product of sums form by writing one sum term for each output 0. The sum terms are expressed by writing complement of a variable when it appears as an input 1 and the variable itself when it appears as an input 0. Consider, for example, the truth Table 1.3.3.

The sum corresponding to input combinations 010 is $A + \overline{B} + C$, and the sum corresponding to input 101 is $\overline{A} + B + \overline{C}$. Thus, the standard product of sum form is

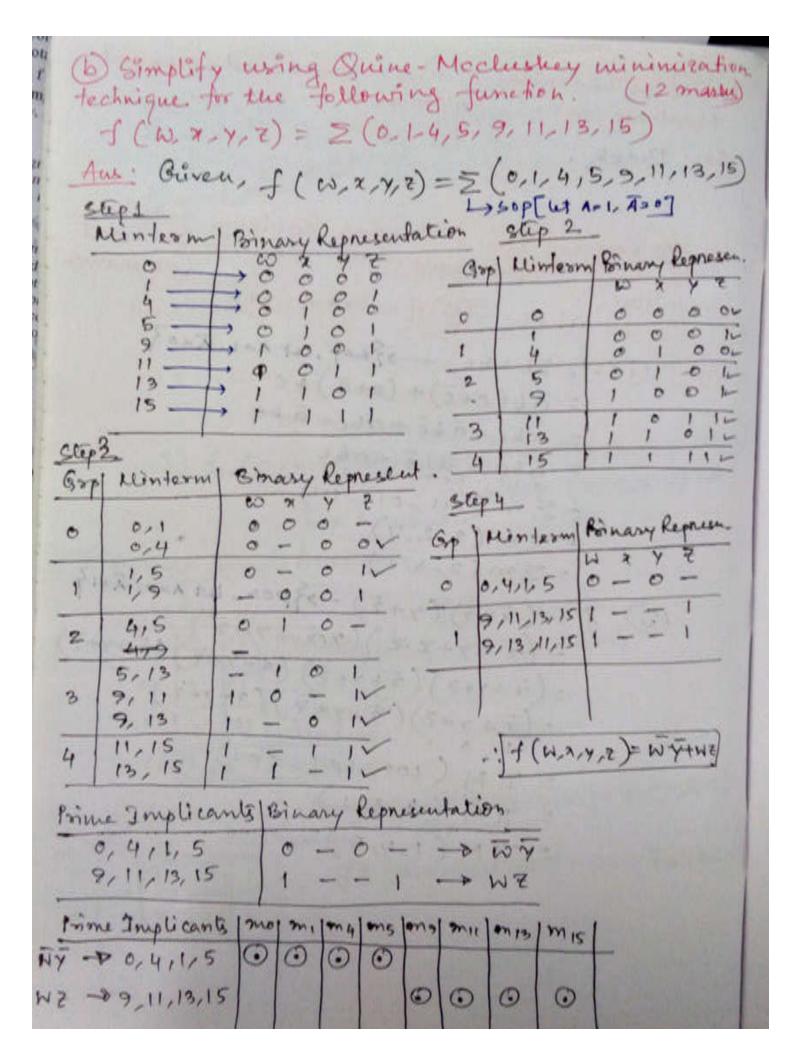
$$f(A, B, C) = (A + \overline{B} + C) (\overline{A} + B + \overline{C})$$

= $M_2 \cdot M_5$

A	В	c	Y	86 Emint
0	0	0	1	mg and as a
0	0	1	1	col function
0	1	0	0	← A + B +
0	_	1		
1	0	0	1	DWDUS ST
1	0	1	0	←A + B + (
1	1	0	1	ME AT STEEL
1	1	1	1	subscript l

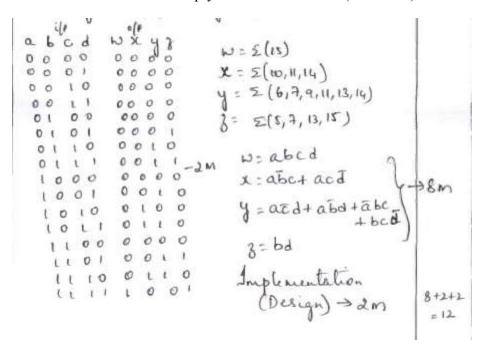
Table 133

2. a) Convert the following Boolean function into their proper canonical form in decimal () f= ab+bc (v)f=(a+y)(y+z) (08 marly) notation. Aus: (1) - = ab+bc -> 5=0p, let A=1, A=03 = ab(c+c)+(a+a)bc = abc + abc + abc + abc = abc + abc + abc = Zm (011,010,111) 25m'(3,2,7) Em (2,3,7) = x (0,1,4,5,6)) f = (\(\bar{2} + \gamma\) (\gamma + \bar{2}) -> \(\bar{2}\) pos, let A=0, \(\bar{A} = 1\bar{2}\) = (ガナソナマを)(メガナソナを) =(マナソナを)(マナソナを)(マナソナを)(マナソナを) =(え+y+を)(え+y+を)(マ+y+を) = TIM (100,101,001) = TIM (4,5,1) = TIM (1,4,5)= E(0,2,3,6,2).

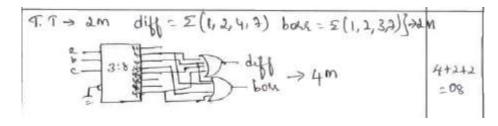


Module-2

3) a) Design a combinational circuit that will multiply two 2-bit numbers. (12 Marks)

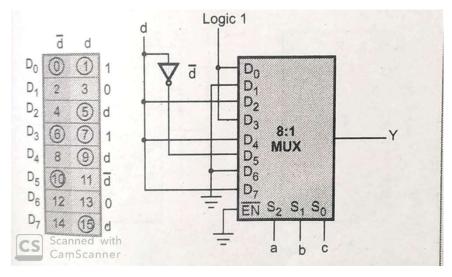


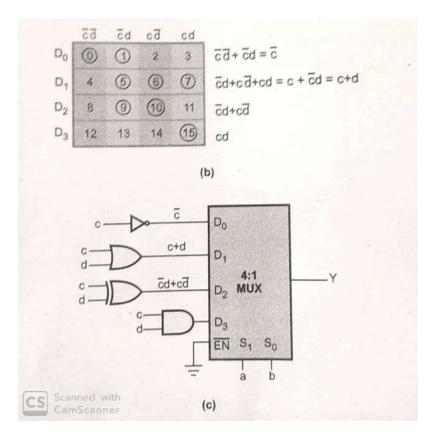
b) Implement full subtractor using 3:8 line decoder with active high outputs and active low enable input. (08 Marks)



OR

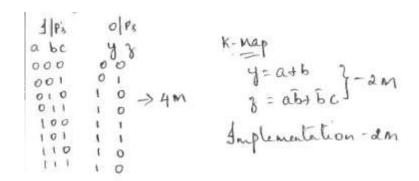
4) a) Implement following using 8 to 1 MUX with a, b, c as select lines $f(a,b,c,d) = \sum (0,1,5,6,7,9,10,15)$. (08 Marks)





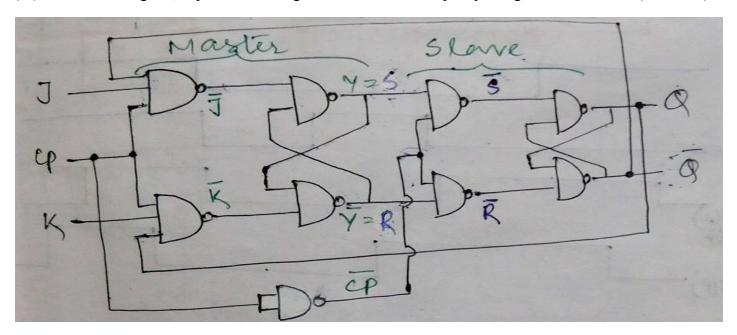
b) Implement a 1-bit comparator using 2:4 decoder 74139. (04 Marks)

c) Design a priority encoder for a system with three inputs, with the middle bit with highest priority encoding to 10, the MSB with the next priority encoding to 11, while the LSB with the least priority encoding to 01. (08 Marks)



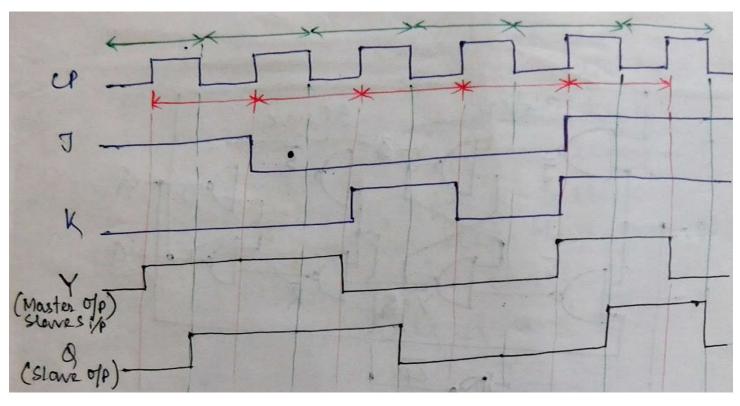
Module-3

5) a) With a neat diagram, explain the workig of master-slave JK flip-flop along with waveforms. (10 Marks)

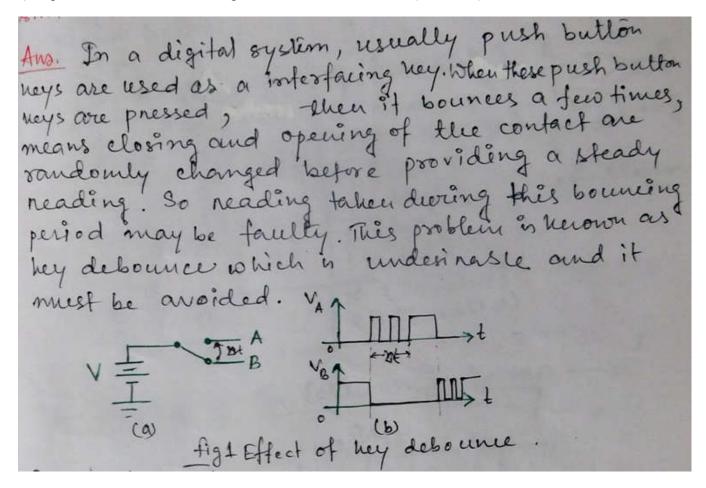


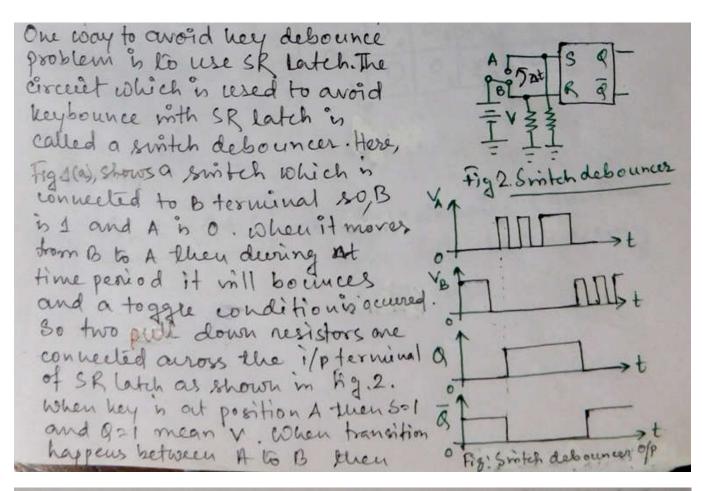
tig. shows the Jk master slave thep thep which consiste of 2 flip-flops named as one s Master another is slave. Slave always follows master. Doth the Hip-flops are positive level triggered but an inverter is connected to the clock input of the sleve flipflop which forces et to to geger at the negative level. Therefore, the information present at the Jandy imputs is transmitted to the ofp of master flighting on the positive clock pulse and 91 ° is held there until the negative doch pulse occurs, after which it in allowed to pass this ush to the output of the slowe of means slowe flip-flop uses the SR input at the negative clock pulse to deler nine its ofp state a and a.

Case(I): when , J= K=0, the gn. of p of master remains Q (NC) same at the +ve clock. (I) JL O (RESET) Thus the ofp of slerve also 1 (SET) remains same at the 10) -Q (Toggle) IT (B) -ve clock. Case(I): When, J=0 & u=1 The master nesely on the +ve clock. The high y ofp of master goes to the Ri/p of the slave. So, at -ve clock slave nesels, again copying the action of the master. case (w): when, J = 1 & u >0, the master sets on the positive clock. The high Y ofp of masks drives the 5°1/p of the sleve, so at - reclark, slave sets, copying the action of master. case(1): When, J= K=1, master toggtes on the positive electe and slave then copies the ofp of master on the negative clock.



b) Explain switch debouncer using SR latch with waveforms. (10 Marks)



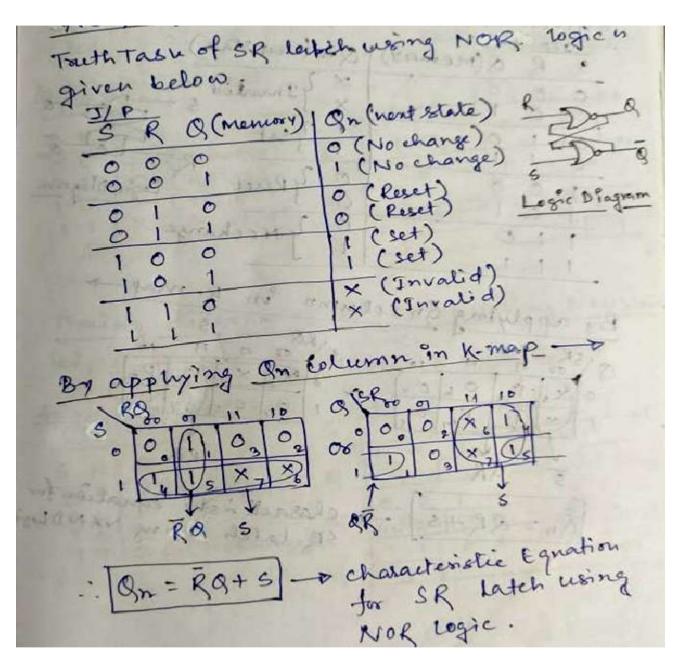


it will take some time (let nsee.). During that time position A and B both are in high impedance state (means low convent will flow). Due to there resistors (pull down) these high impedances are prelled down to gero. So cohemever the contact point is down to gero. So cohemever the contact point is in between A and B then i/p of SR latch will be retoever which will maintain the steady state ofp of the latch.

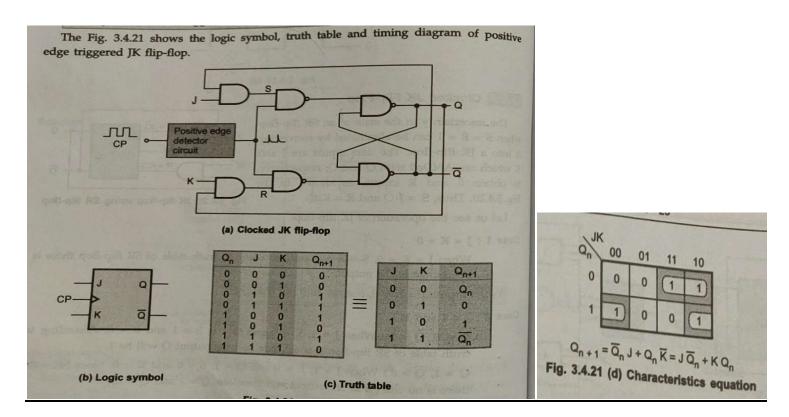
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6) a) Write the characteristic equation of SR, JK, D and T flip-flops. (08 Marks)

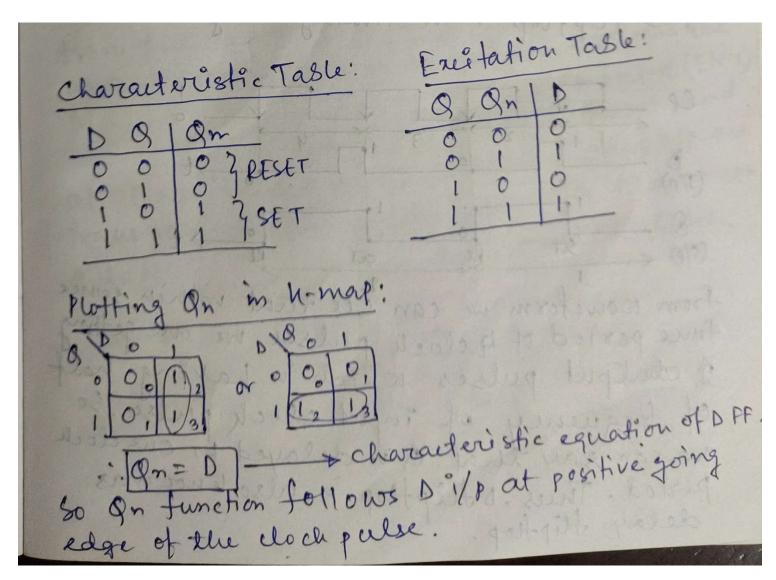
Ans: Characteristics equation of SR flip-flop:



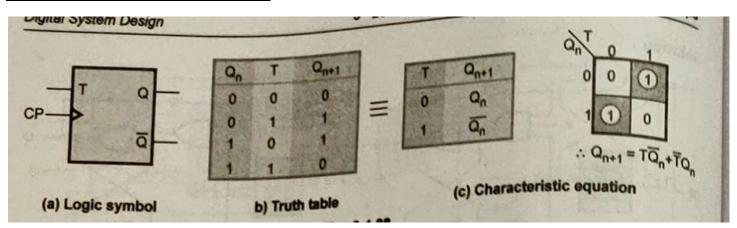
Characteristics equation of JK flip-flop:



Characteristics equation of D flip-flop:



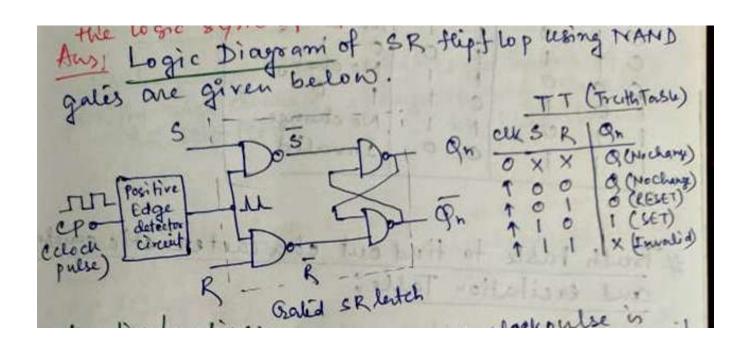
Characteristics equation of T flip-flop:



b) Differentiate sequential logic circuit and combinational logic circuit. (04 Marks)

Sequential Circuit Comsinational Circuits (3) In these a nuits, the (2) In these circuits, the output variables depend olitput variables are at not only on the present all fines dependent on input variensles bid they the combination of 1/P also depend upon the Variables past history of tuese (1) Memory unit is not input variables. required in these issuits. (4) Memory unit's required mese are faster in speed to store the past of hout variables in these circuite because the delay between input and output is due (w) These are slower to propagation delay of than the conscirational galis circuits 1 These circuits are harder to design. Example: Serial Enample!

c) Explain the operation of SR latch with an example. (08 Marks)



case(2): when, cp =0 means, no clark pulse is at the applied, then input will not effect the circuit applied, then input will not be shown at the so memory (Q) element will be shown at the ofp (Qn = next state) means no change it a 1st row care (1) when, S= R=0 and cp = 1 means lk

Pulse is applied then again like SR gated

Indicate 2 of it is I show No change i. e gn=0. Thus

Indicate 2 of the show No change i. e gn=0. Thus indicates 2 and so w of Truth Task. ase (a): when, S=0, R=1 & clock pulse is
applied then at of present (and) condition
will be reflected. This indicates the 3rd rowof Case(a): When, S=1, R=0 & clock pulse in applied
Then aid ofp it mill show cet (Qn=1) condition. This indicates the 4 rth row of TT. then of off it will show undefined or invalid

Module-4

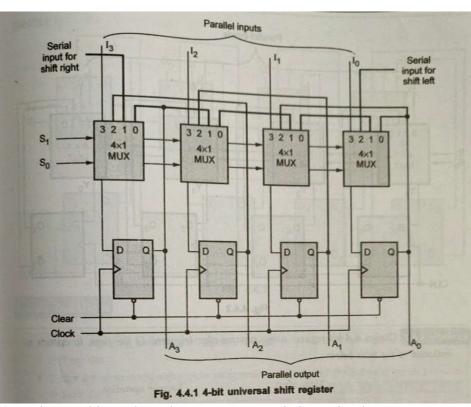
7) a) Design a 4-bit register using positive edge triggered D-flip-flop to operate as indicated in the tablebelow: (12 Marks)

Mod	de Select	Data line selected	Register Operation		
a_1	a_0				
0	0	d_0	Hold		
0	1	d_1	Shift right		
1	0	d_2	Shift left		
1	1	d_3	Parallel load		

Ans:

A register capable of shifting in one direction only is a unidirectional shift register. A register capable of shifting in both directions is a bidirectional shift register. If the register has both shifts (right shift and left shift) and parallel load capabilities, it is referred to as Universal shift register.

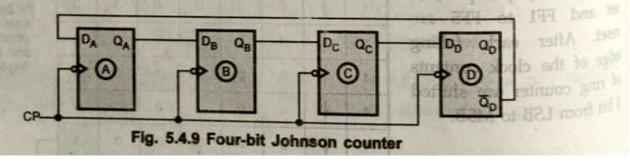
The Fig. 4.4.1 shows the 4-bit universal shift register. It has all the capabilities listed above. It consists of four flip-flops and four multiplexers. The four multiplexers have two common selection inputs S_1 and S_0 , and they select appropriate input for D flip-flop. The Table 4.4.1 shows the register operation depending on the selection inputs of multiplexers. When $S_1S_0=00$, input 0 is selected and the present value of the register is applied to the D inputs of the flip-flops. This results no change in the register value. When $S_1S_0=01$, input 1 is selected and circuit connections are such that it operates as a right shift register. When $S_1S_0=10$, input 2 is selected and circuit connections are such that it operates as a left shift register. Finally, when $S_1S_0=11$, the binary information on the parallel input lines is transferred into the register simultaneously and it is a parallel load operation.



Mode	Select	Data line	Register		
a_1	a_0	selected	Operation		
0	0	d_0	Hold		
0	1	d_1	Shift right		
1	0	d_2	Shift left		
1	1	d_3	Parallel load		

b) Design a 4-bit mod-8 Johnson counter and also write the count sequence table. (08 Marks)

In a Johnson counter, the Q output of each stage of flip-flop is connected to the D input of the next stage. The single exception is that the complement output of the last flip-flop is connected back to the D-input of the first flip-flop as shown in Fig. 5.4.9.



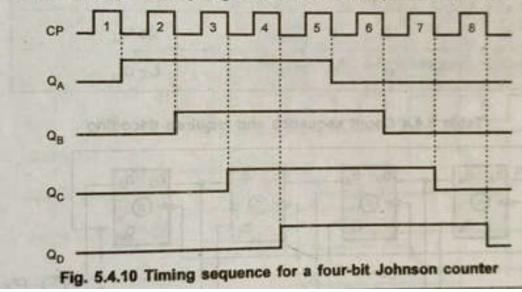
As shown in Fig. 5.4.9 there is a feedback from the rightmost flip-flop complement output to the leftmost flip-flop input. This arrangement produces a unique sequence of states.

Initially, the register (all flip-flops) is cleared. So all the outputs, QA, QB, QC, QD are zero. The output of last stage, QD is zero. Therefore complement output of last stage, QD is one. This is connected back to the D input of first stage. So DA is one. The first falling clock Table 5.4.2 Four-bit Johnson sequence edge produces $Q_A = 1$ and $Q_B = 0, Q_C = 0$,

Clock pulse	QA	Qg	Qc	Qo
0	0	0	0	07
1	1	0	0	0
2	1	1	0	0
3	1	1	1	0
4	1	1	1	1
5	0	1	1	1
6	0	0	1	1/
7	0	0	0	11

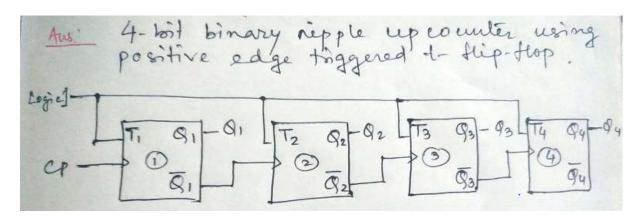
 $Q_D = 0$ since D_B , D_C , D_D are zero. The next clock pulse produces $Q_A = 1$, $Q_B = 1$, $Q_C = 0$, QD = 0. The sequence of states is summarized in Table 5.4.2. After 8 states the same sequence is repeated.

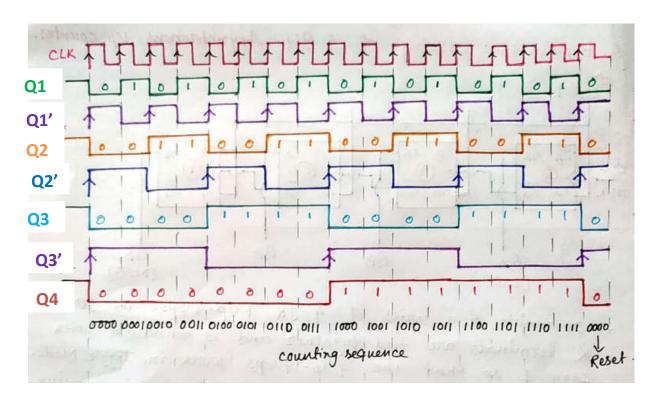
In this case, four-bit register is used. So the four-bit sequence has a total of eight states. Fig. 5.4.10 gives the timing sequence for a four-bit Johnson counter.

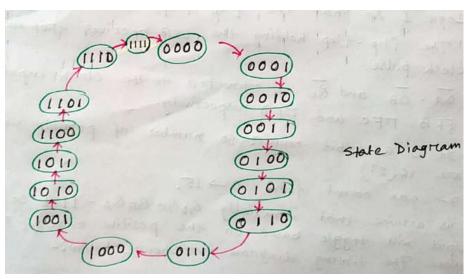


OR

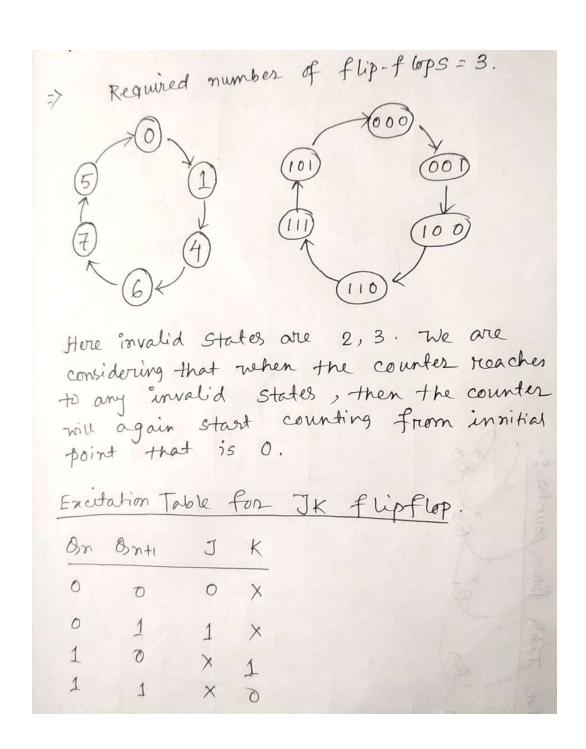
8) a) Design a 4-bit binary ripple up counter using positive edge triggered t-flipflop with a count enable line. Write the counting sequence and relevant timing diagram.



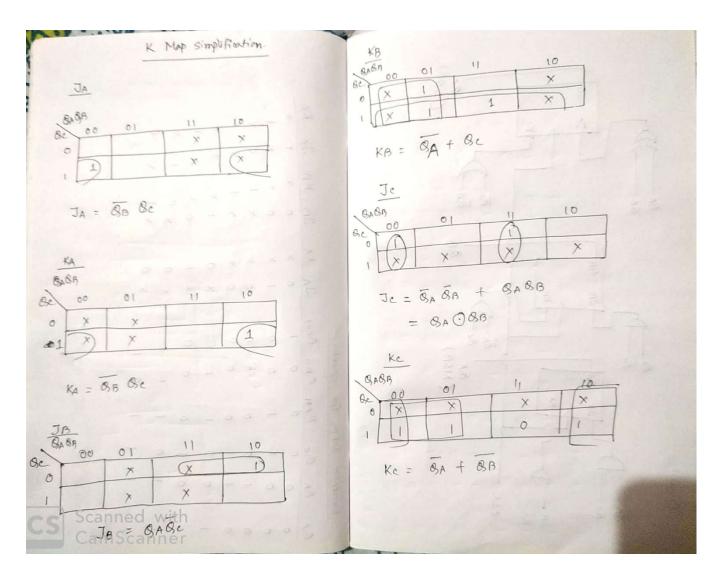


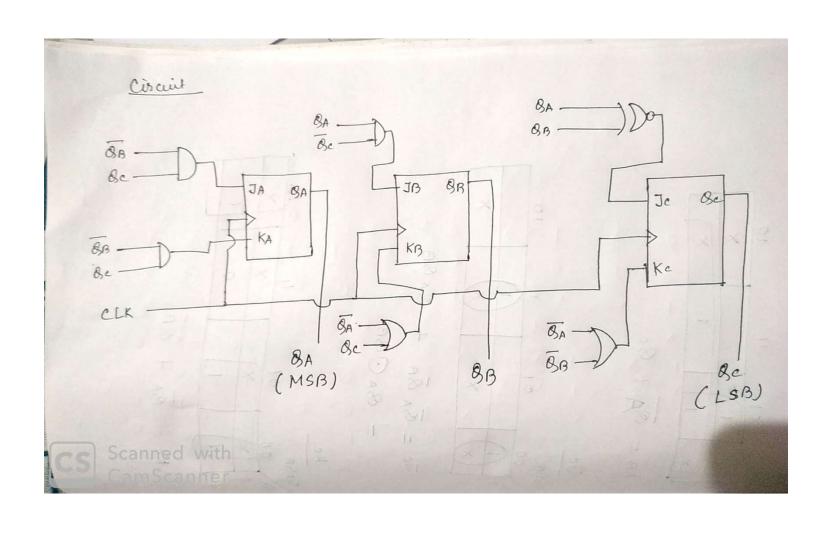


(b) Design a synchronous counter to count the sequence 0, 1, 4, 6, 7, 5 and repeatusing positive edge triggered JK flip-flops.



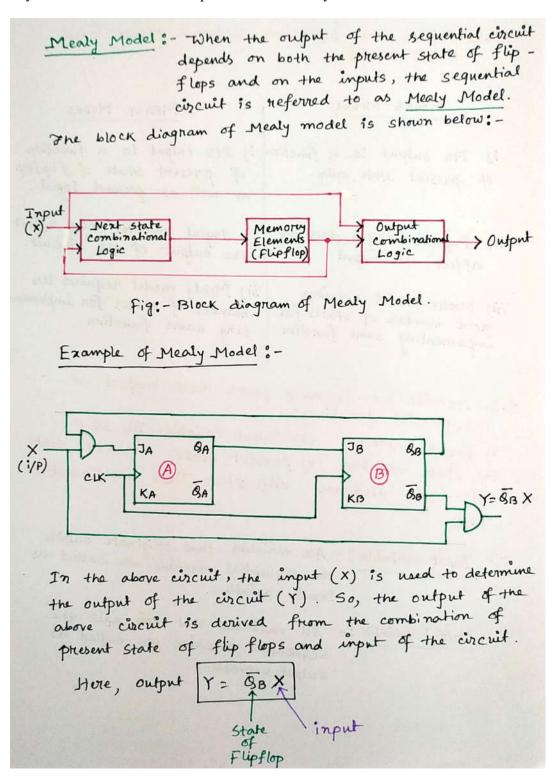
BA	SB	Bc_	BAH	SB+1	BC+1	JA	KA	JB	KB	Jc	Kc
0	. 0	0	0	0	1	0	×	0	×	1	×
0	0	1	1	0	0	1	×	0	×	×	-1
0		0	0	0	0	0	×	×	1	0	X
0	1	1	0	0	0	0	×	×	1.	X	F
	0	0	1	ı	0	×	0	1	×	0	X
1		1	D	0	0	×	1	0	X	×	1
de l	0	^	1			×	0	×	2	1	×
		ed with	1	0 1		×	0	X.	1	X	D

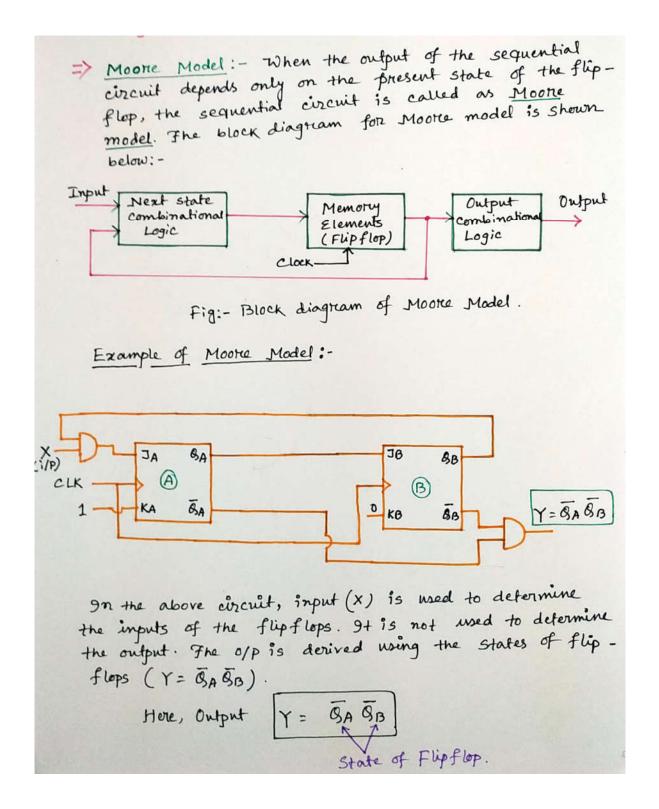




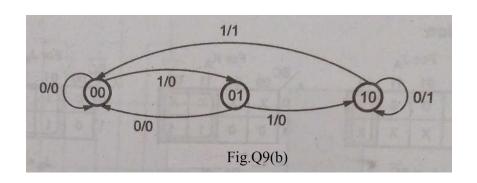
Module-4

9) a) Explain Mealy and Moore model in a sequential circuit analysis.

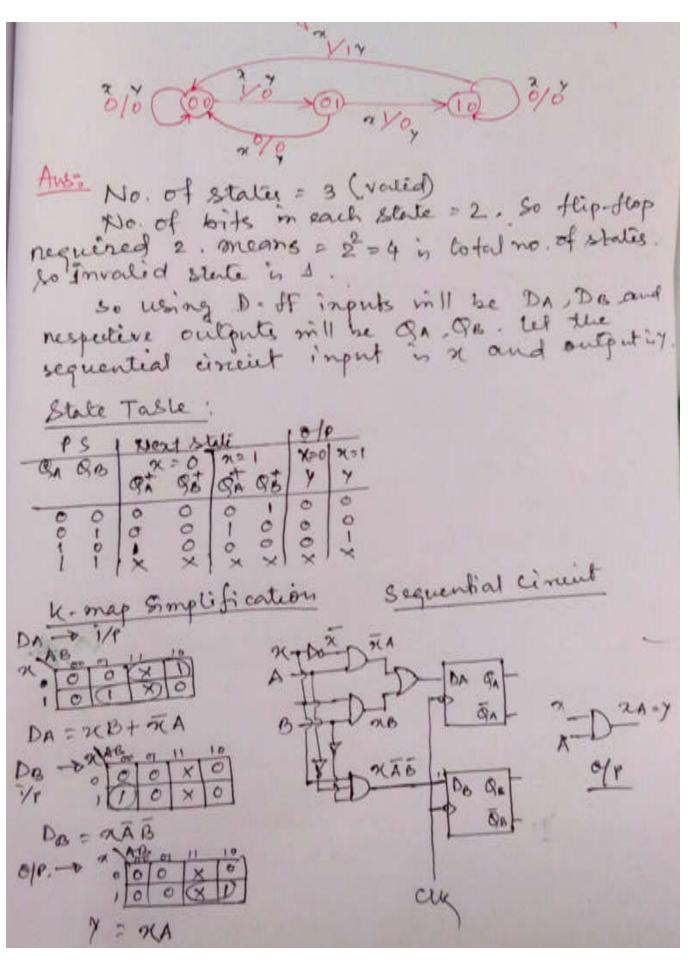




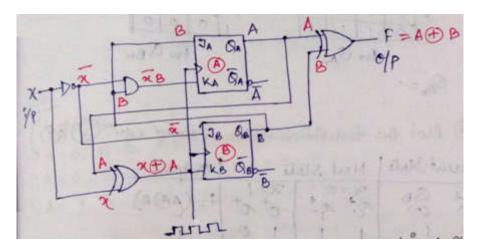
b) Design a sequential circuit using D-flip-flop for the state diagram. Show below in Fig.Q9(b). (12 Marks)



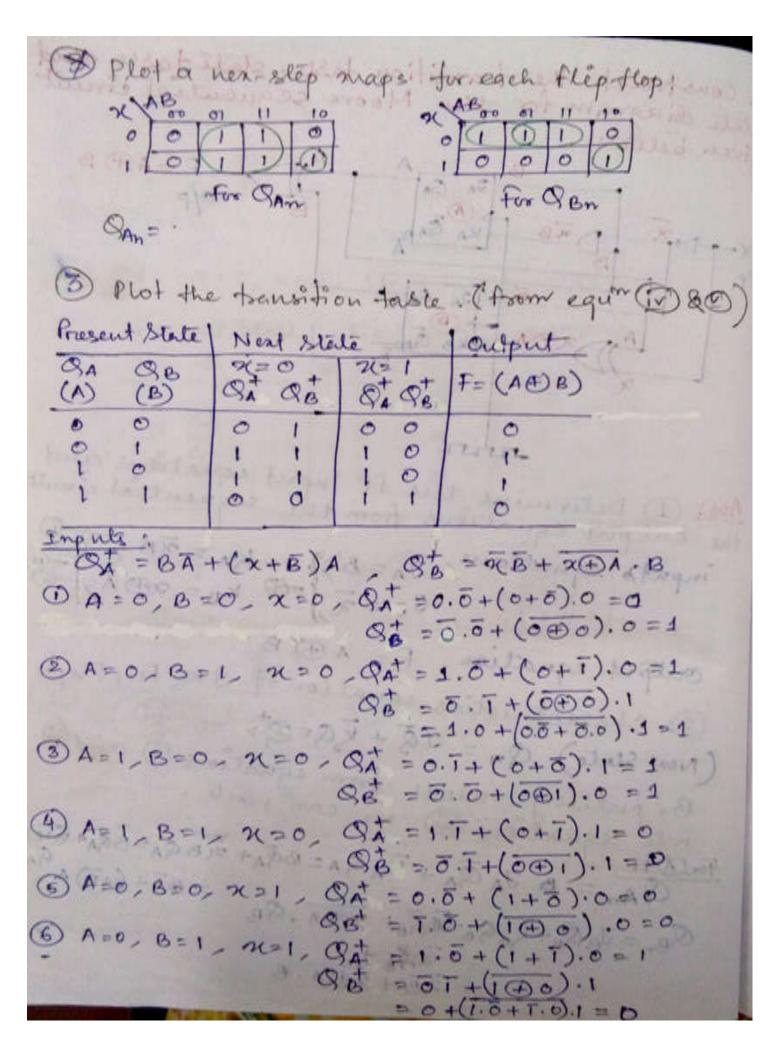
Ans.



10) a) Construct the excitation table, transition table, state table and state diagram for the Moore sequential circuit shown in Fig.Q10(a).



Aw: (1) Determine the ff input equations and the output equations from the sequential circuit. inputs equations, JA=B, KA=XB, -0 Joseph Kos QA A TO output equation, $F = A \oplus B$ 2 characteristics equation of JK flip Flogin (Next state) Qn = Jg + Kg=Qt - W By putting values from equations (1) and (i) into equations (ii) we can write. For & flipflop: QB = JBQB+KBQB QA = JA QA+KAQA = 208+ 20A.QB =BQA+XBQA = 7B+ XDA.B - (F) = BA + (x+B). A - (V) Transition equations are (i) and (1)



b) Write short notes on: i) ROM, ii) RAM, iii) EPROM, iv) Flash Memory.

Read Only Memories (ROM)

- We can't write data in read only memories. It is non-volatile memory i.e. it can hold data even if
 power is turned off. Generally, ROM is used to store the binary codes for the sequence of instructions
 you want the computer to carry out and data such as look up tables. This is because this type of
 information does not change.
- It is important to note that although we give the name RAM to static and dynamic read/write memory devices, that does not mean that the ROMs that we are using are also not random access devices. In fact, most ROMs are accessed randomly with unique addresses.
- The Fig. 6.4.1 shows the typical configuration of a ROM cell. It consists of a transistor T and switch P.
- The transistor T is driven by the word line. The contents of cell can be read from the cell when word line is logic 1. A logic value 0 is read if the transistor is connected to ground through switch P. If switch P is open, a logic value 1 is read. The bit line is connected through a resistor to the power supply. A sense circuit at the end of the bit line generates the proper output value. Data is stored into a ROM when it is manufactured.
- There are four types of ROM: Masked ROM, PROM, EPROM and EEPROM or E²PROM.

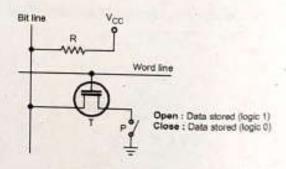


Fig. 6.4.1 ROM cell

Random Access Memory (RAM) / Read-Write Memories

- The memory in which the time taken to transfer information to or from any desired random location is always the same is called random access memory.
- · There are two types of RAMs :
 - Static RAM
 Dynamic RAM

Static RAM (SRAM)

Memories that consists of circuits capable of retaining their state as long as power is applied are known as static memories. These are Random Access Memory (RAM) and hence combinely called static RAM memories.

 Fig. 6.3.1 shows the one-bit memory cell for static RAM. The storage part of the cell is modeled by an SR latch with associated gates to form a D latch.

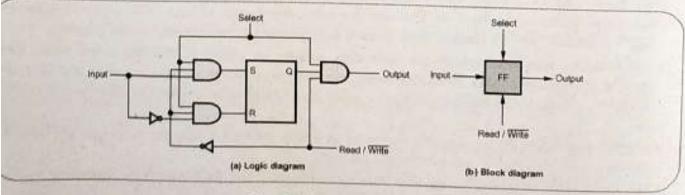


Fig. 6.3.1 One-bit binary cell

- The binary cell is capable of storing one bit in its internal latch.
- The select input enables the cell for reading and writing, and the read/write input determines the
 operation of the cell when it is selected.
- When Read/Write input is logic 1, read operation is performed; otherwise, write operation is performed.

Dynamic RAM (DRAM)

Dynamic RAM Cell

• Dynamic RAM stores the data as a charge on the capacitor. Fig. 6.3.2 shows the dynamic RAM cell. A dynamic RAM contains thousands of such memory cells. When COLUMN (Sense) and ROW (Control) lines go high, the MOSFET conducts and charges the capacitor. When the COLUMN and ROW lines go low, the MOSFET opens and the capacitor retains its charge. In this way, it stores 1 bit. Since only a single MOSFET and capacitor are needed, the dynamic RAM contains more memory cells as compared to static RAM per unit area.

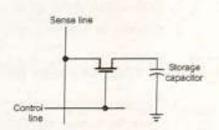


Fig. 6.3.2 Dynamic RAM

 The disadvantage of dynamic RAM is that it needs refreshing of charge on the capacitor after every few milliseconds. This complicates the system design, since it requires the extra hardware to control refreshing of dynamic RAMs.

EPROM (Erasable Programmable Read Only Memory)

- Erasable programmable ROMs use MOS circuitry. They store I's and 0's as a packet of charge in a buried layer of the IC chip. EPROMs can be programmed by the user with a special EPROM programmer. The important point is that we can erase the stored data in the EPROMs by exposing the chip to ultraviolet light through its quartz window for 15 to 20 minutes, as shown in the Fig. 6.4.4.
- It is not possible to erase selective information, when erased the entire information is lost. The chip can be reprogrammed. This memory is ideally suitable for product development,

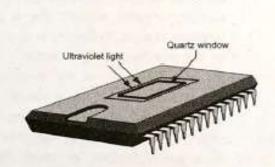


Fig. 6.4.4 EPROM

experimental projects and college laboratories, since this chip can be reused many times, over.

EPROM Programming:

- When erased each cell in the EPROM contains 1. Data is introduced by selectively programming 0's into the desired bit locations. Although only 0's will be programmed, both 1's and 0's can be presented in the data.
- During programming address and data are applied to address and data pins of the EPROM. When the address and data are stable, program pulse is applied to the program input of the EPROM. The program pulse duration is around 50 ms and its amplitude depends on EPROM IC. It is typically 5.5 V to 25 V. In EPROM, it is possible to program any location at any time - either individually, sequentially, or at random.

Flash Memory

Flash memories are read/write memories. In flash memories it is possible to read the contents of a single cell, but it is only possible to write an entire block of cells. A flash cell is based on a single transistor controlled by trapped charge.

A typical flash memory cell uses a floating gate to store a bit by the presence or absence of a charge. If the floating gate is not charged (i.e. neutral), then the device operates almost like a normal MOSFET, a positive charge in the control gate creates a channel in the p-substrate that carries a current from source to drain. If however the floating gate is negatively

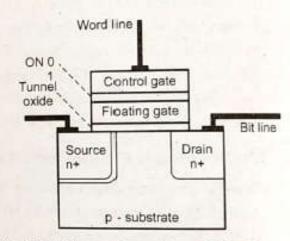


Fig. 6.4.5 Storage transistor with floating gate

charged, then this charge shields the channel region somewhat from the control gate and prevents the formation of a channel between source and drain. The threshold voltage is the voltage applied to the control gate at which a transistor becomes conductive. The presence or the absence of a charge results in a more positive or more negative threshold voltage. In flash memory, programming (putting electrons into the floating gate) means writing a 0, erasing (removing the charge from the floating gate) means resetting the flash memory contents to 1.

The floating gate is completely surrounded by an isolation layer. This enables the floating gate transistor to be used as non-volatile memory.

Advantages and Drawbacks

Disadvantage: Editing Ability: A computer can read a specific byte from any address on the flash chip, but it can only erase and rewrite in block units.

Disadvantage: Lifetime: Flash memory does not have an infinite lifetime. It can only endure about 100,000 program/erase cycles.

Advantage: Efficiency: Because flash memory stores data without the use of moving mechanical parts, its operation requires less energy than older systems. Flash memory also stores data much more compactly than a hard drive can.